

# Switching (−30V, −5.0A)

## RSS050P03

**●Features**

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (SOP8).

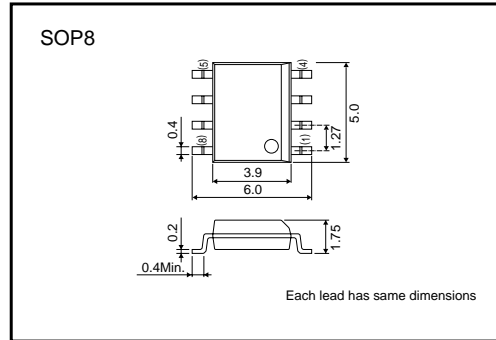
**●Application**

Power switching, DC / DC converter.

**●Structure**

Silicon P-channel  
MOS FET

**●External dimensions (Unit : mm)**



**●Packaging specifications**

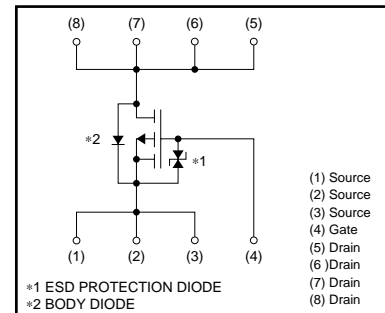
Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RSS050P03		○

**●Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Drain-source voltage	V <sub>DSS</sub>	−30	V
Gate-source voltage	V <sub>GSS</sub>	±20	V
Drain current	Continuous	I <sub>D</sub>	±5.0 A
	Pulsed	I <sub>DP</sub>	±20 A *1
Source current (Body diode)	Continuous	I <sub>S</sub>	−1.6 A
	Pulsed	I <sub>SP</sub>	−20 A *1
Total power dissipation	P <sub>D</sub>	2.0	W *2
Channel temperature	T <sub>ch</sub>	150	°C
Range of Storage temperature	T <sub>stg</sub>	−55 to +150	°C

\*1 P<sub>WM</sub>≤10μs, Duty cycle≤1%  
\*2 Mounted on a ceramic board

**●Equivalent circuit**



**●Thermal resistance (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C / W *

\* Mounted on a ceramic board.

## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	$\pm 10$	$\mu A$	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	–30	–	–	V	$I_D=-1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	–1	$\mu A$	$V_{DS}=-30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	–1.0	–	–2.5	V	$V_{DS}=-10V, I_D=-1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	30	42	$m\Omega$	$I_D=-5.0A, V_{GS}=-10V$
		–	47	65	$m\Omega$	$I_D=-2.5A, V_{GS}=-4.5V$
		–	55	77	$m\Omega$	$I_D=-2.5A, V_{GS}=-4.0V$
Forward transfer admittance	$ Y_{fs} $ *	5.0	–	–	S	$V_{DS}=-10V, I_D=-2.5A$
Input capacitance	$C_{iss}$	–	1200	–	pF	$V_{DS}=-10V$
Output capacitance	$C_{oss}$	–	250	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	–	180	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	12	–	ns	$I_D=-2.5A$
Rise time	$t_r$ *	–	25	–	ns	$V_{DD}=-15V$
Turn-off delay time	$t_{d(off)}$ *	–	70	–	ns	$V_{GS}=-10V$
Fall time	$t_f$ *	–	35	–	ns	$R_L=6\Omega$
Total gate charge	$Q_g$	–	13	–	nC	$V_{DD}=-15V$
Gate-source charge	$Q_{gs}$	–	2.8	–	nC	$V_{GS}=-5V$
Gate-drain charge	$Q_{gd}$	–	5.0	–	nC	$I_D=-5.0A$

\*Pulsed

## Body diode characteristics (source-drain characteristics)

Forward voltage	$V_{SD}$	–	–	–1.2	V	$I_S=-1.6A, V_{GS}=0V$
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Transistors

●Electrical characteristic curves

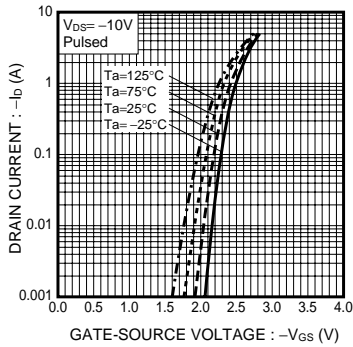


Fig.1 Typical Transfer Characteristics

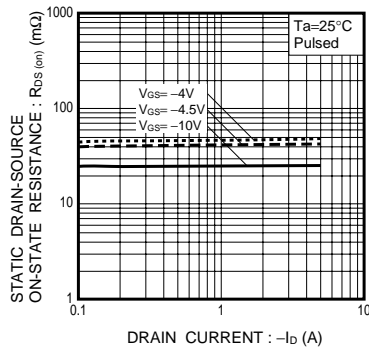


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

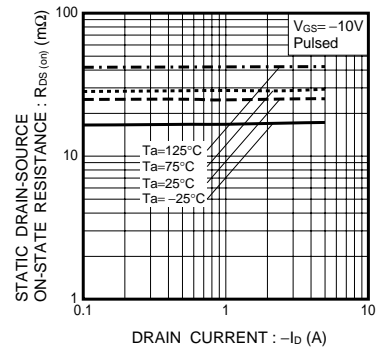


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

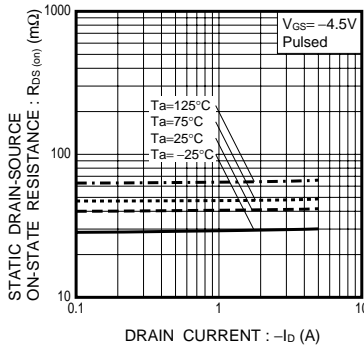


Fig.4 Static Drain-Source On-State vs. Drain Current

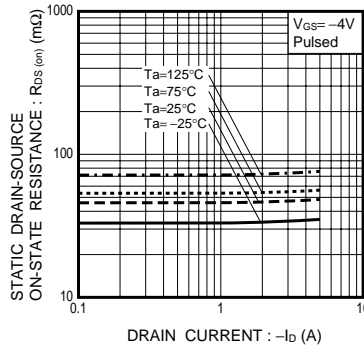


Fig.5 Static Drain-Source On-State vs. Drain Current

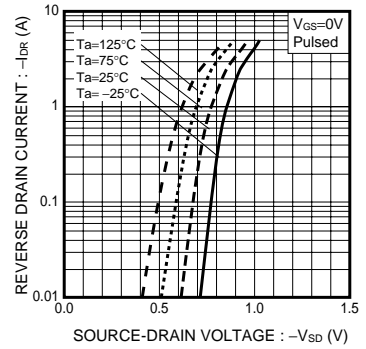


Fig.6 Reverse Drain Current Source-Drain Current

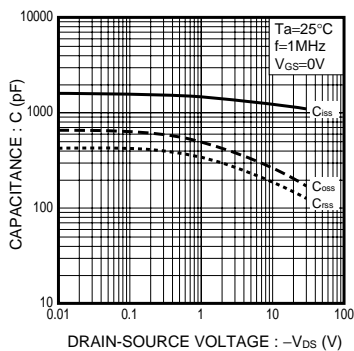


Fig.7 Typical Capacitance vs. Drain-Source Voltage

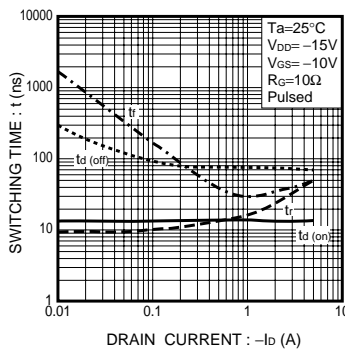


Fig.8 Switching Characteristics

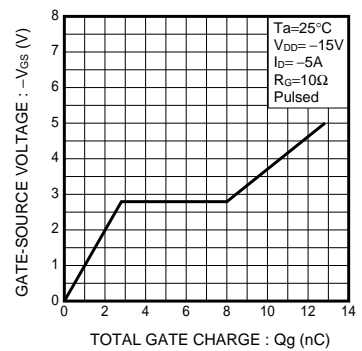


Fig.9 Dynamic Input Characteristics

Transistors

●Measurement circuits

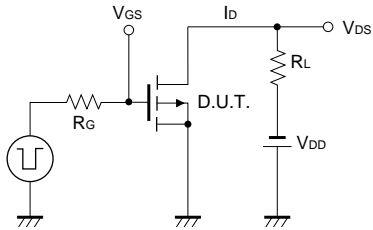


Fig.10 Switching Time Test Circuit

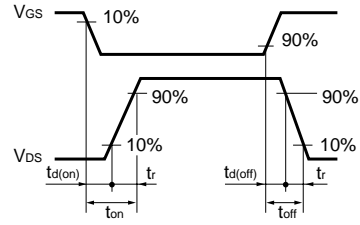


Fig.11 Switching Time Waveforms

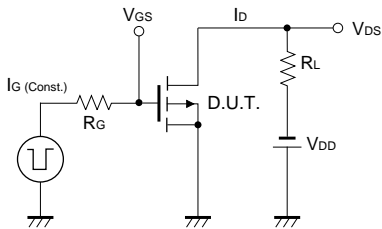


Fig.12 Gate Charge Test Circuit

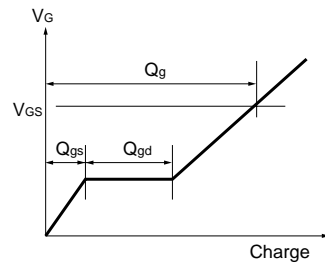


Fig.13 Gate Charge Waveform

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